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NTE96

Silicon NPN Transistor

Power Switching

Absolute Maximum Ratings:

Collector-Base Voltage, V_{CBO} 100V
Collector-Emitter Voltage, V_{CEO} 100V
Emitter-Base Voltage, V_{EBO} 6V
Collector Current, I_C 7A
Total Power Dissipation ($T_C = +25^\circ\text{C}$), P_D 60W
Operating Junction Temperature Range, $T_{j(\text{oper})}$ -65° to $+200^\circ\text{C}$
Storage Temperature Range, T_{stg} -65° to $+200^\circ\text{C}$

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Typical Forward Current Gain	h_{FE}	$I_C = 2A$, $V_{CE} = 2V$	60	–	240	
Collector-Emitter Saturation Voltage	$V_{CE(\text{SAT})}$	$I_C = 7A$, $I_B = 0.7A$	–	1.2	–	V
Transition Frequency	f_T		30	–	–	MHz

